TF252TH



http://onsemi.com

N-Channel JFET 20V, 140 to 350μA, 1.4mS, VTFP

Features

- High gain : GV=1.0dB typ (VCC=2V, RL=2.2kΩ, Cin=5pF, VIN=10mV, f=1kHz)
- · Ultrasmall package facilitates miniaturization in end products
- Best suited for use in electret condenser microphone for audio equipments and telephones
- · Excellent voltage characteristics
- Excellent transient characteristics
- · Adoption of FBET process
- · Halogen free compliance

Specifications

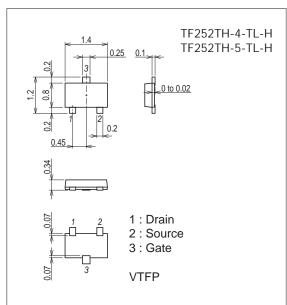
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Gate-to-Drain Voltage	V _{GDO}		-20	V
Gate Current	IG		10	mA
Drain Current	ID		1	mA
Allowable Power Dissipation	PD		100	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

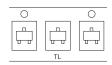
unit : mm (typ) 7031A-001



Product & Package Information

Package : VTFP
JEITA, JEDEC : SC-106A
Minimum Packing Quantity : 8,000 pcs./reel

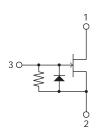
Packing Type: TL



Marking



Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Gate-to-Drain Breakdown Voltage	V(BR)GDO	IG=-100μA	-20			V	
Cutoff Voltage	V _{GS} (off)	V _{DS} =2V, I _D =1μA	-0.1	-0.4	-1.0	V	
Drain Current	IDSS	V _{DS} =2V, V _{GS} =0V	140*		350*	μΑ	
Forward Transfer Admittance	yfs	V _{DS} =2V, V _{GS} =0V, f=1kHz	0.8	1.4		mS	
Input Capacitance	Ciss	V== 2V_V== 0V f 1MI =		3.1		pF	
Reverse Transfer Capacitance	Crss	VDS=2V, VGS=0V, f=1MHz		0.95		pF	
[Ta=25°C, V _{CC} =2.0V, R _L =2.2kΩ, Cin=5pF, See specified Test Circuit.]							
Voltage Gain	GV	V _{IN} =10mV, f=1kHz		1.0		dB	
Reduced Voltage Characteristic	ΔGVV	V _{IN} =10mV, f=1kHz, V _{CC} =2.0V → 1.5V		-0.6	-2.0	dB	
Frequency Characteristic	ΔGvf	f=1kHz to 110Hz			-1.0	dB	
Total Harmonic Distortion	THD	V _{IN} =30mV, f=1kHz		0.65		%	
Output Noise Voltage	V _{NO}	V _{IN} =0V, A curve		-106	-102	dB	

* : The TF252TH is classified by IDSS as follows : (unit : $\mu A)$

Rank	4	5		
IDSS	140 to 240	210 to 350		

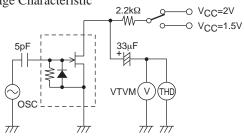
Test Circuit

Voltage gain

Frequency Characteristic

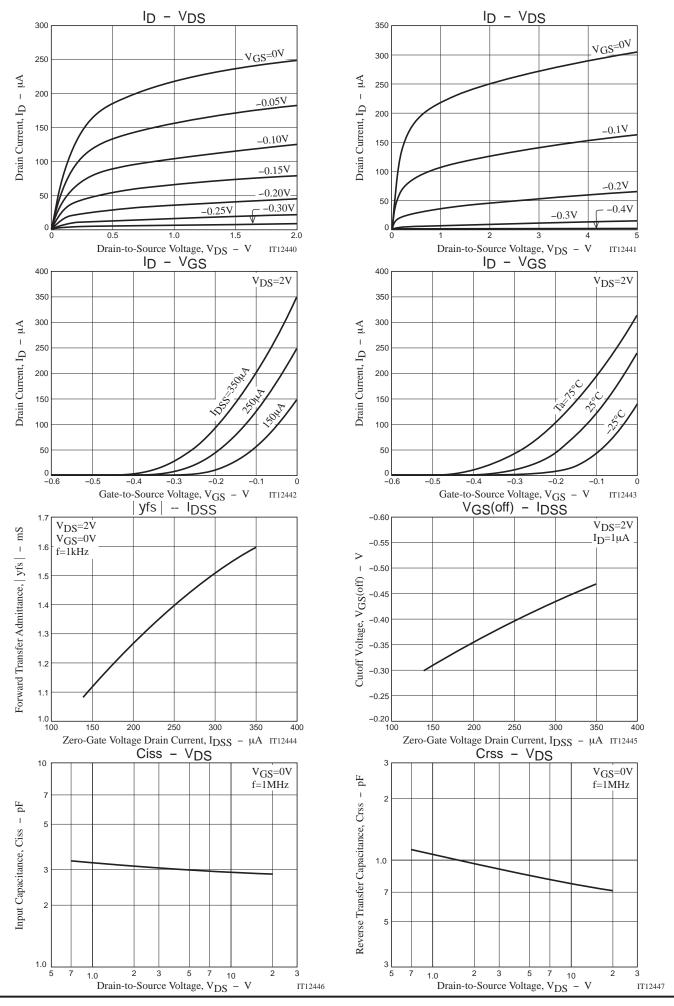
Distortion

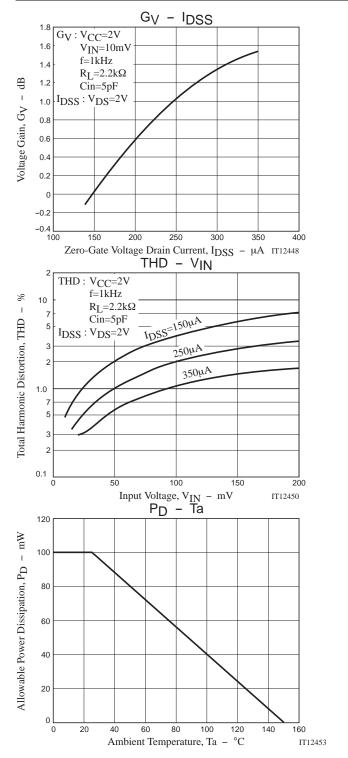
Reduced Voltage Characteristic

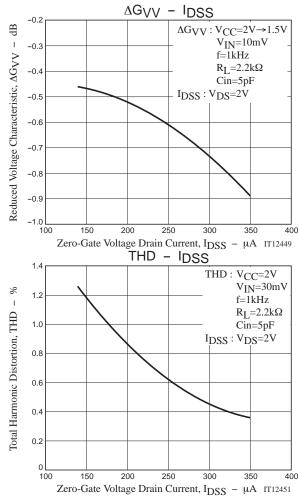


Ordering Information

Device	Package	Shipping	memo	
TF252TH-4-TL-H	VTFP	8,000pcs./reel	Db Free and Helegen Free	
TF252TH-5-TL-H	VTFP	8,000pcs./reel	Pb Free and Halogen Free	





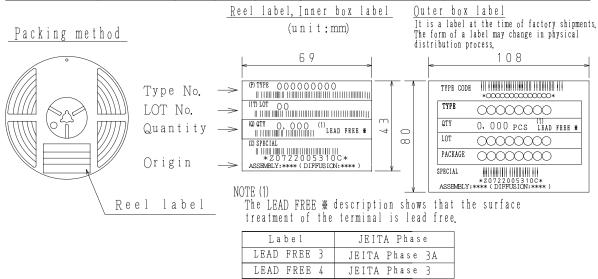


Taping Specification

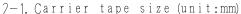
TF252TH-4-TL-H, TF252TH-5-TL-H

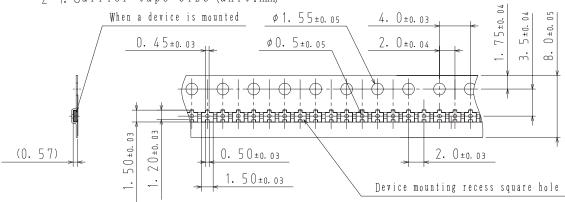
1. Packing Format

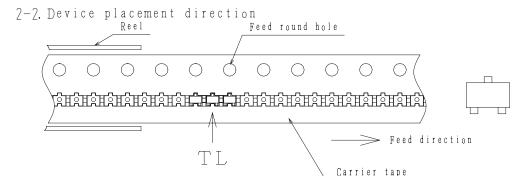
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
VTFP	VSFP	8,000	40,000	240,000	5 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		



2. Taping configuration





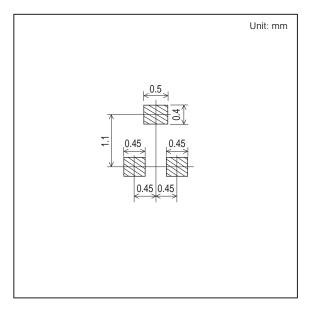


Those with oen electrode terminal on the feed hole side·····TL

Outline Drawing

TF252TH-4-TL-H, TF252TH-5-TL-H

Land Pattern Example



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